ALPHA & OMEGA SEMICONDUCTOR

AO4852

60V Dual N-Channel MOSFET

General Description

The AO4852 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. As a pair these MOSFETs operate very efficiently in Push Pull and Bridge topologies.

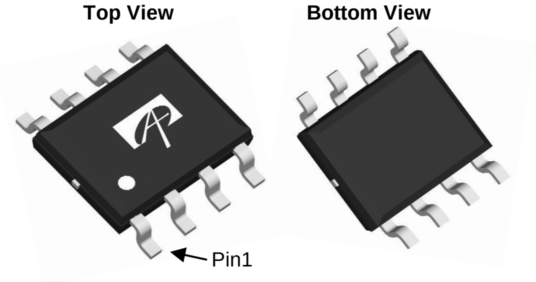
Product Summary

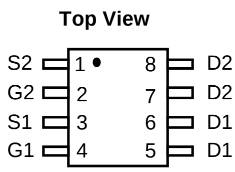
V_{DS} (V) = 60V
I_D = 3.5A (V$_{GS}$ = 10V)
$R_{DS(ON)}$ <90mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ <105mΩ (V_{GS} = 4.5V)

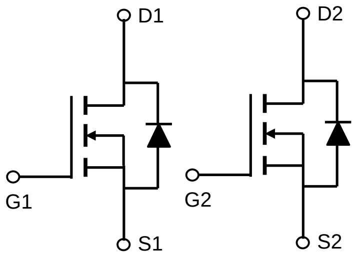
100% UIS Tested
100% Rg Tested

Green Product

SOIC-8







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum 10 Sec	Maximum Steady State	Units
Drain-Source Voltage		V_{DS}	60		V
Gate-Source Voltage		V_{GS}	±20		V
Continuous Drain Current [A]	T_A=25°C	I_D	3.5	3	A
	T_A=70°C		2.8	2.4	
Pulsed Drain Current [B]		I_{DM}	20		
Power Dissipation	T_A=25°C	P_D	2	1.4	W
	T_A=70°C		1.3	0.9	
Avalanche Current [B]		I_{AR}	8		A
Repetitive avalanche energy 0.3mH [B]		E_{AR}	9.6		mJ
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		74	90	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	33	40	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		60			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V				100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		1.7	2.3	2.6	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V		20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=3A			79	90	mΩ
			T_J=125°C		146	159	
		V_{GS}=4.5V, I_D=2A			86	105	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=3A			15		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.8	1	V
I_{SM}	Pulsed Body-Diode Current[B]					20	A
I_S	Maximum Body-Diode Continuous Current					2.5	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, f=1MHz			372	450	pF
C_{oss}	Output Capacitance				31		pF
C_{rss}	Reverse Transfer Capacitance				17		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			1.7	2.6	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=3A			7.1	9.2	nC
Q_g(4.5V)	Total Gate Charge				3.6		nC
Q_{gs}	Gate Source Charge				1		nC
Q_{gd}	Gate Drain Charge				2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=30V, R_L=10Ω, R_{GEN}=3Ω			4.1	5.3	ns
t_r	Turn-On Rise Time				2.1		ns
$t_{D(off)}$	Turn-Off DelayTime				15		ns
t_f	Turn-Off Fall Time				2.1		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=3A, dI/dt=100A/µs			23.4	29	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=3A, dI/dt=100A/µs			23.2		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using < 300 µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.
Rev1: Nov. 2010

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

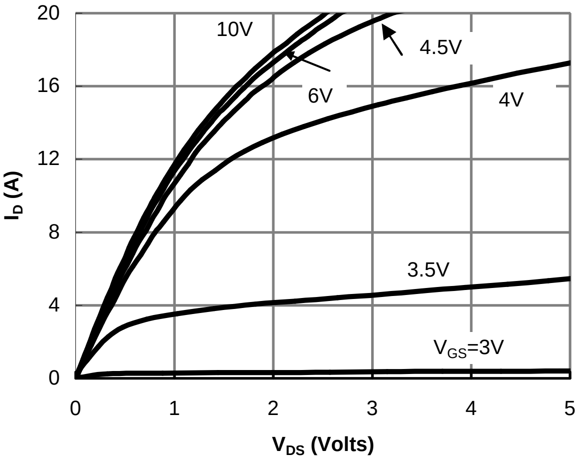


Fig 1: On-Region Characteristics

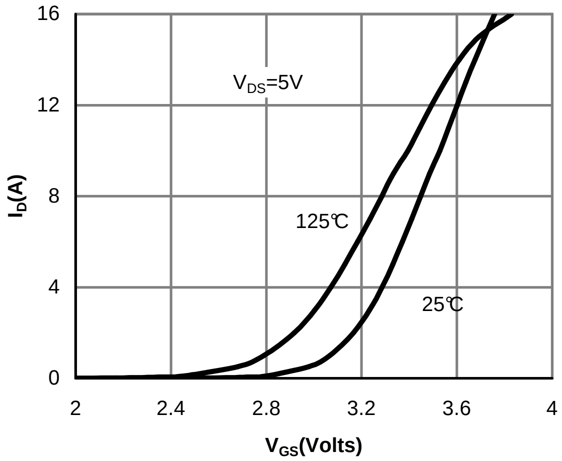


Figure 2: Transfer Characteristics

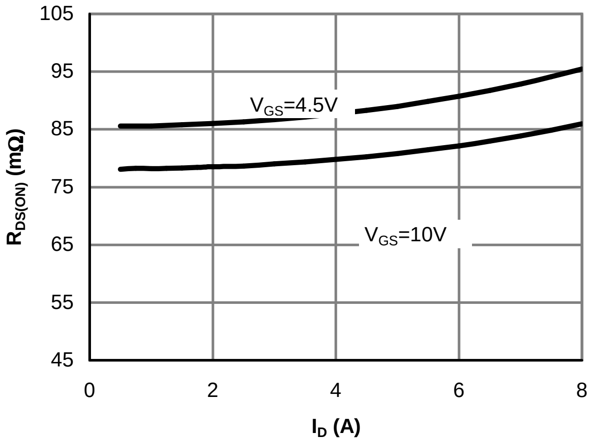


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

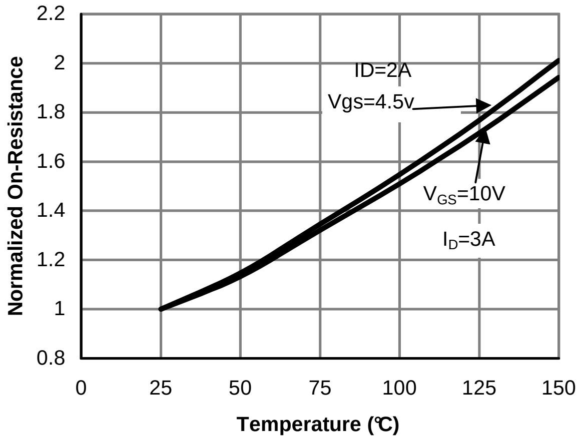


Figure 4: On-Resistance vs. Junction Temperature

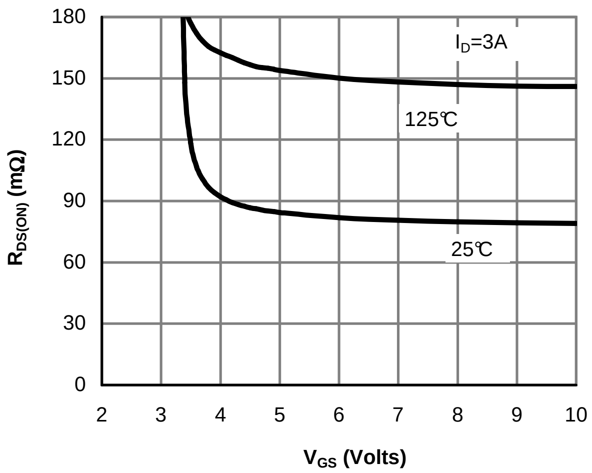


Figure 5: On-Resistance vs. Gate-Source Voltage

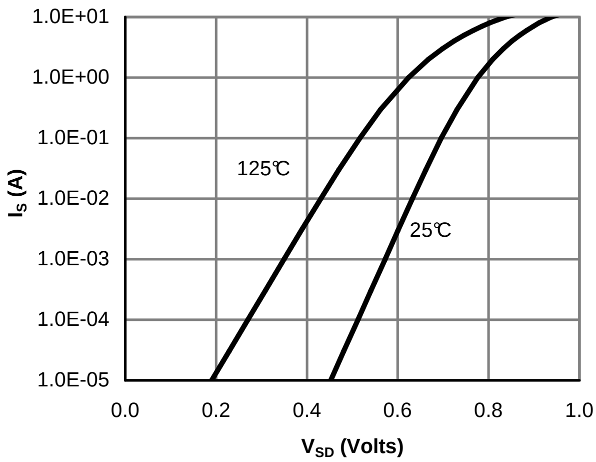


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

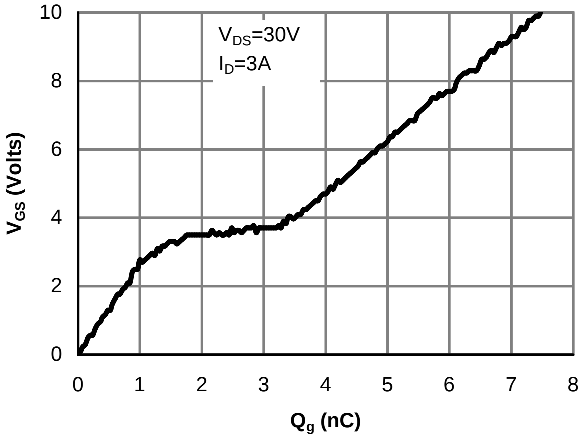


Figure 7: Gate-Charge Characteristics

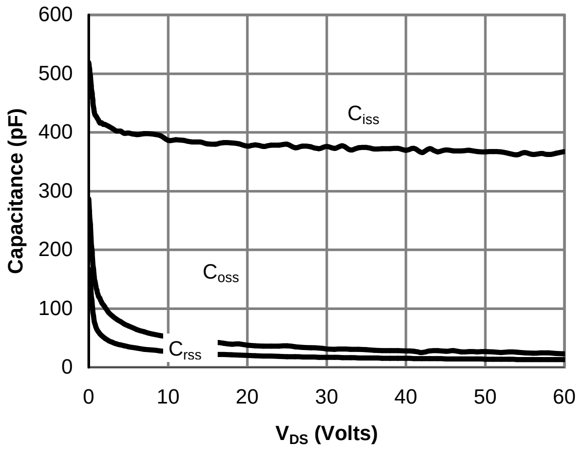


Figure 8: Capacitance Characteristics

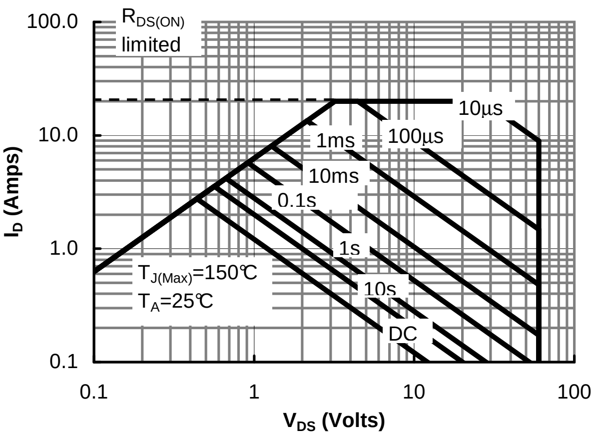


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

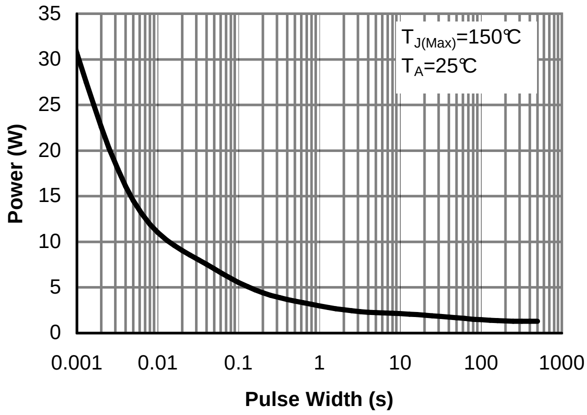


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

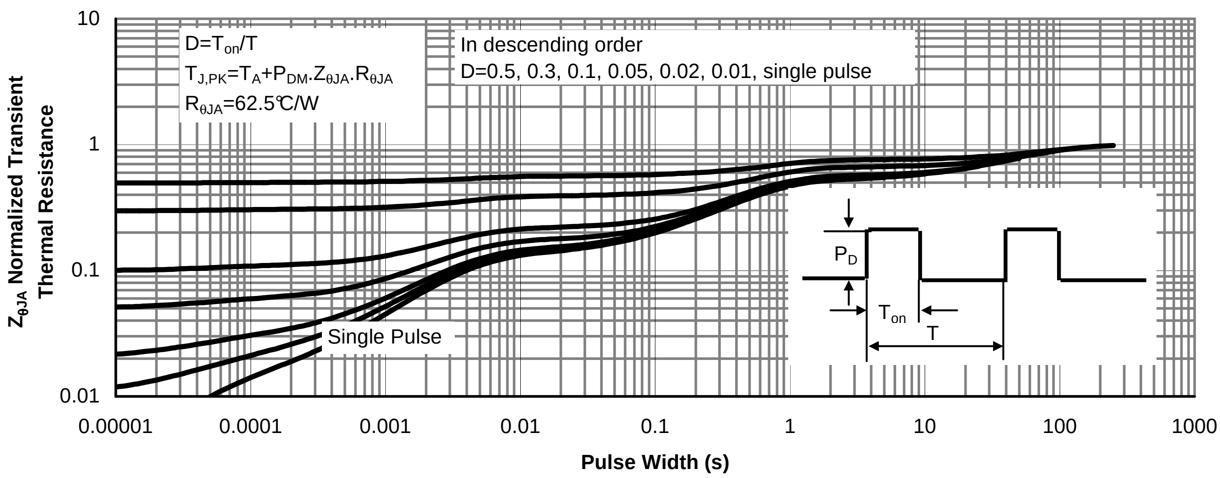


Figure 11: Normalized Maximum Transient Thermal Impedance